

BLAKELY SOKOLOFF TAYLOR & ZAFMAN

A LIMITED LIABILITY PARTNERSHIP INCLUDING LAW CORPORATIONS

TELEPHONE (408) 720-8300

FACSIMILE (408) 720-8383

BSTZ_MAIL@BSTZ.COM

WWW.BSTZ.COM

INTELLECTUAL PROPERTY LAW

SILICON VALLEY

1279 OAKMEAD PARKWAY
SUNNYVALE, CALIFORNIA 94085-4040

OTHER OFFICES

LOS ANGELES, CA
ORANGE COUNTY/COSTA MESA, CA
DENVER, CO
PORTLAND/BEAVERTON, OR
SEATTLE, WA

August 24, 2007

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450


Re: **CERTIFICATE OF CORRECTION**
U. S. Letters Patent No. 7,153,784
Issued: December 26, 2006
For: **METHOD FOR MAKING A SEMICONDUCTOR
DEVICE HAVING A HIGH-K GATE
DIELECTRIC LAYER AND A METAL GATE
ELECTRODE**
Inventor: Brask, et al.
Our File No. 42390.P18609

Dear Sir:

Enclosed is the Certificate of Correction (two copies) for the above-referenced patent.
This request for correction is made under rule 322 of the Rules of Practice and 35 U.S.C.
Section 254.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP



Edwin H. Taylor
Reg. No. 25,129

EHT/sn
Enclosures

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,153,784

DATED : December 26, 2006

INVENTOR(S) : Brask et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 13, at line 5, delete "suicide" and insert --silicide--.

MAILING ADDRESS OF SENDER
BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN
1279 Oakmead Parkway
Sunnyvale, CA 94085-4040

PATENT NO. 7,153,784

Certificate of Correction (PTO Form 1050)-Amended